



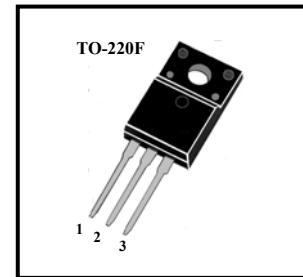
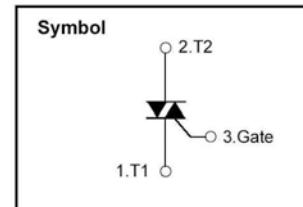
**Shantou Huashan Electronic Devices Co.,Ltd.**

**HBT137F-600**

### INSULATED TYPE TRIAC (TO-220F PACKAGE)

#### ■ Features

- \* Repetitive Peak Off-State Voltage: 600V
- \* R.M.S On-State Current( $I_{T(RMS)}=8A$ )
- \* High Commutation dv/dt
- \* Isolation Voltage (V<sub>ISO</sub>=1500V AC)



#### ■ General Description

This device is fully isolated package suitable for AC switching application, phase control application such as fan speed and temperature modulation control, lighting control and static switching relay.

#### ■ Absolute Maximum Ratings ( $T_a=25^\circ C$ )

$T_{stg}$ — Storage Temperature	.....	-40~150°C
$T_j$ — Operating Junction Temperature	.....	-40~125°C
$P_{GM}$ — Peak Gate Power Dissipation	.....	5W
$V_{DRM}$ — Repetitive Peak Off-State Voltage	.....	600V
$I_T$ (RMS) — R.M.S On-State Current ( $T_c=76^\circ C$ )	.....	8.0A
$V_{GM}$ — Peak Gate Voltage	.....	10V
$I_{GM}$ — Peak Gate Current	.....	2.0A
$I_{TSM}$ — Surge On-State Current (One Cycle, 50/60Hz,Peak,Non-Repetitive)	.....	70/77A
$V_{ISO}$ — Isolation Breakdown Voltage (R.M.S, A.C.1minute)	.....	1500V

#### ■ Electrical Characteristics ( $T_a=25^\circ C$ )

Symbol	Items	Min		Max	Unit	Conditions
$I_{DRM}$	Repetitive Peak Off-State Current			1.0	mA	$V_D=V_{DRM}$ , Single Phase, Half Wave, $T_j=125^\circ C$
$V_{TM}$	Peak On-State Voltage			1.6	V	$I_T=10A$ , Inst. Measurement
$I^{+}_{GT1}$	Gate Trigger Current ( I )			25	mA	$V_D=6V$ , $R_L=10$ ohm
$I^{-}_{GT1}$	Gate Trigger Current ( II )			25	mA	$V_D=6V$ , $R_L=10$ ohm
$I^{-}_{GT3}$	Gate Trigger Current ( III )			25	mA	$V_D=6V$ , $R_L=10$ ohm
$V^{+}_{GT1}$	Gate Trigger Voltage ( I )			1.5	V	$V_D=6V$ , $R_L=10$ ohm
$V^{-}_{GT1}$	Gate Trigger Voltage ( II )			1.5	V	$V_D=6V$ , $R_L=10$ ohm
$V^{-}_{GT3}$	Gate Trigger Voltage ( III )			1.5	V	$V_D=6V$ , $R_L=10$ ohm
$V_{GD}$	Non-Trigger Gate Voltage	0.2			V	$T_j=125^\circ C$ , $V_D=1/2V_{DRM}$
$(dv/dt)_c$	Critical Rate of Rise of Off-State Voltage at Commutation	5.0			V/ $\mu$ s	$T_j=125^\circ C$ , $V_D=2/3V_{DRM}$ $(di/dt)_c=-3A/ms$
$I_H$	Holding Current		10		mA	
$R_{th(j-c)}$	Thermal Resistance			3.8	°C/W	Junction to case



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## ■ Performance Curves

Fig 1. Gate Characteristics

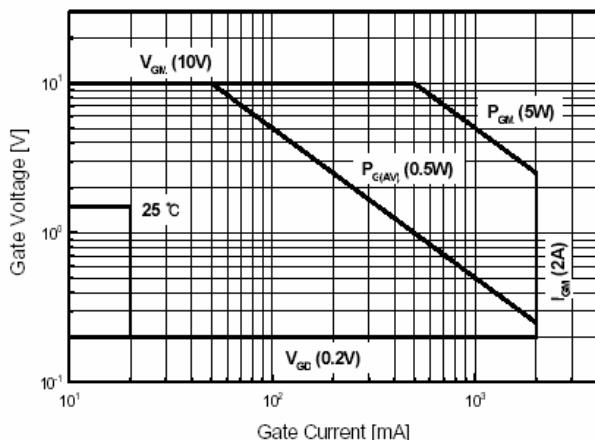


Fig 2. On-State Voltage

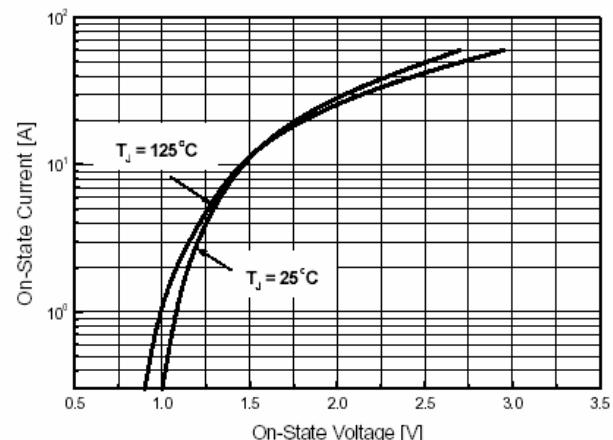


Fig 3. On State Current vs.  
Maximum Power Dissipation

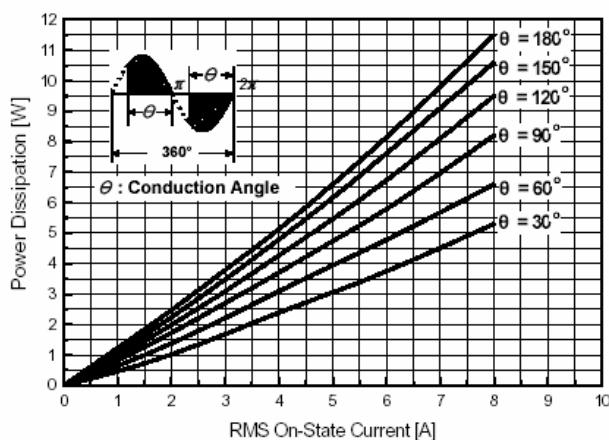


Fig 4. On State Current vs.  
Allowable Case Temperature

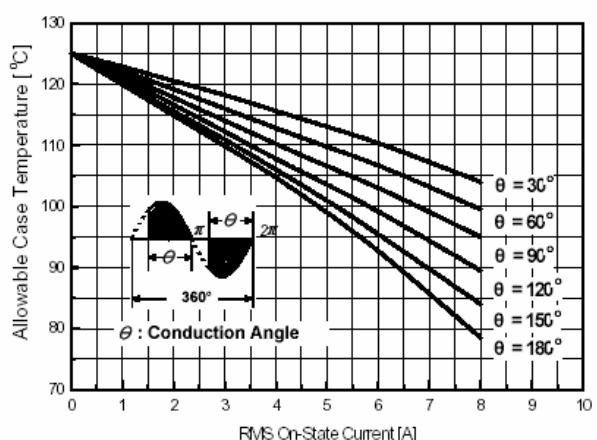


Fig 5. Surge On-State Current Rating  
( Non-Repetitive )

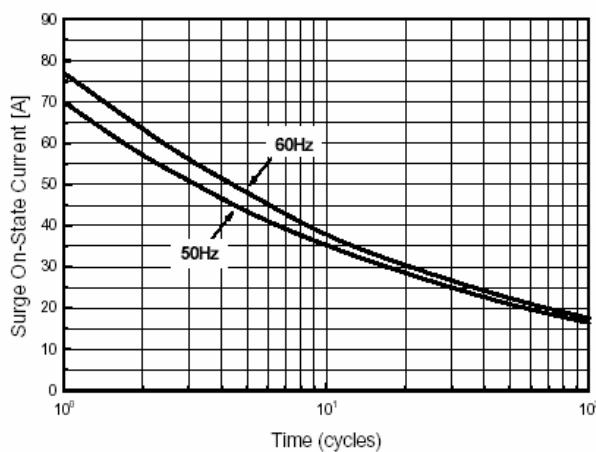
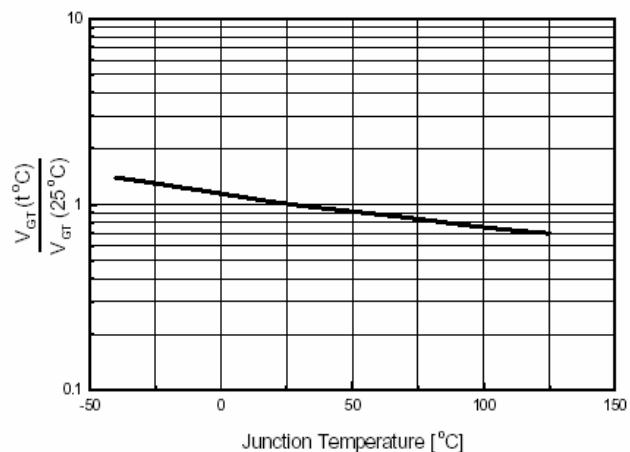


Fig 6. Gate Trigger Voltage vs.  
Junction Temperature





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Fig 7. Gate Trigger Current vs.  
Junction Temperature

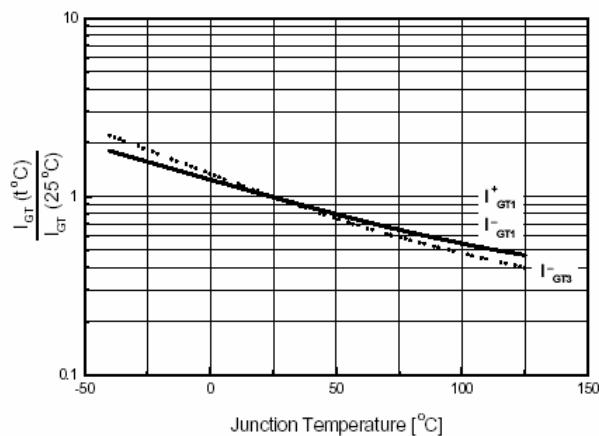


Fig 8. Transient Thermal Impedance

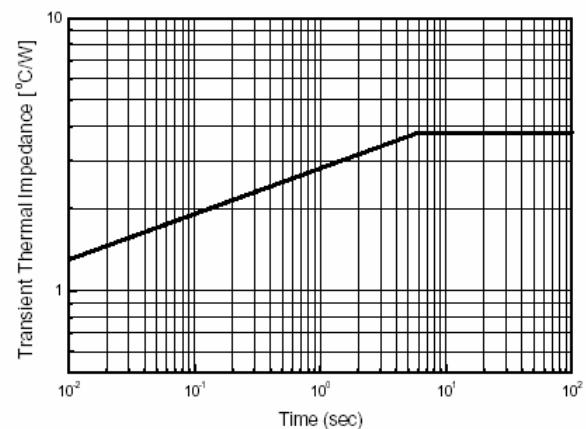


Fig 9. Gate Trigger Characteristics Test Circuit

